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Vishay/Siliconix DG2034DN-T1-E4

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DG2034

Vishay Siliconix

Single 4:1 Low r_{ON} Multiplexers

DESCRIPTION

The DG2034 is a low voltage, low r_{ON} , high bandwidth single 4 to 1 analog multiplexer designed for high performance switching of analog and video signals. Combining low power; fast switching; low on-resistance, flatness and matching; and small physical size, the DG2034 is ideal for portable and battery applications.

Built on Vishay Siliconix's low voltage CMOS process, the DG2034 has an epitaxial layer which prevents latchup. Break-before-make is guaranteed.

FEATURES

- Low voltage operation (1.8 V to 5.5 V)
- Low on-resistance $r_{DS(on)}$: 4 Ω
- Off-isolation and crosstalk: 55 dB at 10 MHz
- Fast switch 25 ns t_{ON}
- Low charge injection Q_{IN.I}: 4.7 pC
- Low power consumption 4 μW

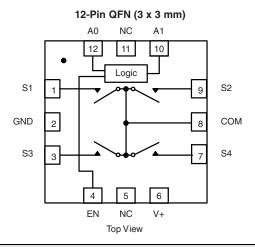
BENEFITS

- High accuracy
- · High bandwidth
- · TTL and low voltage logic compatibility
- Low power consumption
- · Reduced PCB space

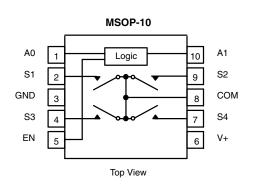
APPLICATIONS

- · Mixed signal routing
- · Portable and battery operated systems
- · Low voltage data acquisition
- Modems
- PCMCIA cards

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE						
A1	A0	EN	ON Switch			
Х	X	0	None			
0	0	1	S1			
0	1	1	S2			
1	0	1	S3			
1	1	1	S4			



ORDERING INFORMATION					
Temp Range	Package	Part Number			
- 40 °C to 85 °C	MSOP-10	DG2034DQ-T1-E3			
	12-pin QFN (3 x 3 mm)	DG2034DN-T1-E4			

Document Number: 72418 S-80164-Rev. D, 28-Jan-08



Datasheet of DG2034DN-T1-E4 - IC MULTIPLEXER 4X1 12QFN

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ABSOLUTE MAXIMUM RATINGS						
Parameter		Limit	Unit			
Referenced V+ to GND	- 0.3 to + 6					
A_X , E_N , S_X , COM^a	- 0.3 to (V+ + 0.3)	V				
Continuous Current (Any Terminal)	± 50	A				
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 100	mA			
QFN-12 (3 x 3 mm) ^c		1295	mW			
Power Dissipation (Packags) ^b	MSOP-10 ^d	320	7 11100			
Storage Temperature (D Suffix)	- 65 to 150	°C				

Notes:

- a. Signals on S_X, D_X, EN or A_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC Board. c. Derate 16.2 mV/°C above 70 °C.

- d. Derate 4.0 mV/°C above 70 °C.

SPECIFICATIONS (V+	= 3 V)							
		Test Conditions Otherwise Unless Specified $V+=3~V,\pm10~\%,~V_{AL}=0.4~V,~V_{AH}=1.5~V^e$			Limits - 40 to 85 °C			
Parameter	Symbol			Temp.a	Min.c	Typ.b	Max.c	Unit
Analog Switch								
Analog Signal Range ^d	V _{ANALOG}			Full	0		V+	V
On-Resistance	r _{ON}			Room Full		4	7 9	
r _{ON} Match	Δr _{ON}	$V+ = 2.7 \text{ V}, V_{COM} = 0.5 \text{ V}/1.5$ $I_{S} = 10 \text{ mA}$	V/2.0 V	Room		0.1	0.3	Ω
r _{ON} Flatness ^{d,f}	r _{ON} Flatness			Room		0.3	1.5	
Off Leakage Current ^g	I _{S(off)}	$V_{+} = 3.3 \text{ V}, V_{S} = 1 \text{ V/3}$ $V_{COM} = 3 \text{ V/1 V}, V_{EN} = 0$	V	Room Full	- 1 - 10	0.3	1 10	
COM Off Leakage Current ^g	I _{COM(off)}) V	Room Full	- 1 - 10	0.3	1 10	nA
Channel-On Leakage Current ^g	I _{COM(on)}	$V_{COM} = V_{S} = 1 \text{ V/3 V}$		Room Full	- 1 - 10	0.3	1 10	
Digital Control								
Input Current ^d	I _A or I _{EN}	$V_{A/EN} = 0$ or V+, See Truth	Table	Full	- 1.0		1.0	μΑ
Input High Voltage ^d	V _{AH} or V _{ENH}			Full	1.5			V
Input Low Voltage ^d	V_{AL} or V_{ENL}			Full			0.4	"
Dynamic Characteristics								
Turn-On Time	t _{ON}			Room Full		25	35 45	
Turn-Off Time	t _{OFF}	$V_{S} = 1.5 \text{ V}, R_{L} = 300 \text{ G}$	2	Room Full		15	25 35	ns
Break-Before-Make Time ^d	t _D			Room		10.5		
Transition Time	t _{trans}	$V_S = 1.5 \text{ V/0 V}, V_S = 0 \text{ V/1.5 V}, F$	$R_L = 300 \Omega$	Room Full		30	45 55	
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } V_{gen} = 0 \text{ V, } R_{gen}$	= 0 Ω	Room		- 4.7		рС
Off-Isolation ^d	OIRR	$R_L = 50 \Omega, C_L = 5 pF$	f = 1 MHz	Room		- 73		
On-isolation	Ollill	ΠΕ = 30 32, ΘΕ = 3 βΙ	f = 10 MHz	Room		- 54		dB
Channel-to-Channel Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$	f = 1 MHz f = 10 MHz	Room Room		- 77 - 59		
Off Capacitance ^d	C _{S(off)}	V+ = 2.7 V, f = 1 MHz		Room		14		
COM Off Capacitance ^d	C _{COM(off)}			Room		46		рF
COM On Capacitance ^d	C _{COM(on)}			Room		67		1 .
Power Supply						<u> </u>		
Power Supply Range	V+				2.7		3.3	V
Power Supply Current ^d	l+	$V+=3.3~V,~V_{A/EN}=0~or~3.3~V,~See~Truth~Table$		Full			1.0	μΑ



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		Test Conditions Otherwise Unless Specified				Limits 40 to 85 °	C	
Parameter	Symbol	V+ = 3 V, ± 10 %, V _{AL} = 0.8 V or \		Temp.a	Min.c	Typ.b	Max.c	Unit
Analog Switch						•		
Analog Signal Range ^d	V _{ANALOG}			Full	0		V+	V
On-Resistance	r _{ON}			Room Full		3	5.5 7	
r _{ON} Match	Δr _{ON}	$V+ = 4.5 \text{ V}, V_{COM} = 1.5 \text{ V}/2.5$ $I_{S} = 10 \text{ mA}$	V/3.5 V	Room		0.16	0.5	Ω
r _{ON} Flatness ^{d,f}	r _{ON} Flatness	,5		Room		0.6	1.5	
Off Leakage Current	I _{S(off)}	V+ = 5.5 V, V _S = 1 V/4.5		Room Full	- 1 - 10	0.5	1 10	
COM Off Leakage Current	I _{COM(off)}	$V_{COM} = 4.5 \text{ V/1 V, } V_{EN} =$	0 V	Room Full	- 1 - 10	0.5	1 10	nA
Channel-On Leakage Current	I _{COM(on)}	$V+ = 5.5 V$, $V_{COM} = V_{S} = 1 V$	//4.5 V	Room Full	- 1 - 10	0.5	1 10	
Digital Control								
Input Current ^d	I _{AH} or I _{ENH}	V_A or $V_{EN} = 0$ or V_{+} , See Trut	th Table	Full	- 1.0		1.0	μΑ
Input High Voltage ^d	V_{AH} or V_{ENH}			Full	2.4			V
Input Low Voltage ^d	V_{AL} or V_{ENL}			Full			0.8	
Dynamic Characteristics								
Turn-On Time	t _{ON}			Room Full		18	30 40	
Turn-Off Time	t _{OFF}	$V_S = 3.0 \text{ V}, R_L = 300 \Omega$	2	Room Full		12	20 30	ns
Break-Before-Make Time ^d	t_{D}			Room		10.5		
Transition Time	t _{trans}	$V_S = 3 \text{ V/0 V}, V_S = 0 \text{ V/3 V}, R_L$	= 300 Ω	Room Full		25	40 50	
Off-Isolation ^d	OIRR	$R_L = 50 \Omega, C_L = 5 p$	f = 1 MHz	Room		- 73		
On-isolation			f = 10 MHz	Room		- 53.5		dB
Channel-to-Channel Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$	f = 1 MHz	Room		- 77		
Charge Injection ^d	Q _{INJ}	f = 10 MHz		Room		- 60.2 - 4.4		рС
Off Capacitance ^d	-	C_L = 1 nF, V_{gen} = 0 V, R_{gen} = 0 Ω V+ = 5 V, f = 1 MHz		Room		13		рС
	C _{S(off)}					43		pF
COM Off Capacitance ^d	C _{COM(off)}			Room		_		
COM On Capacitance ^d	C _{COM(on)}			Room		64		
Power Supply Range	V+				4.5	l	5.5	V
Power Supply Range Power Supply Current	V+ +	V+ = 5.5 V, V _{A/EN} = 0 or 5.5 V, See Truth Table		Full	4.5		1.0	μA

Notes

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- d. Guarantee by design, not subjected to production test.
- e. V_A , E_N = input voltage to perform proper function.
- f. Difference of min and max values.
- g. Guaranteed by 5 V testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Document Number: 72418 S-80164-Rev. D, 28-Jan-08

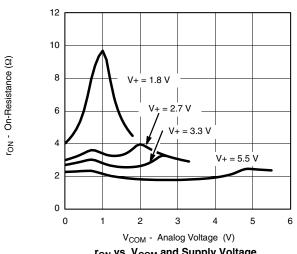


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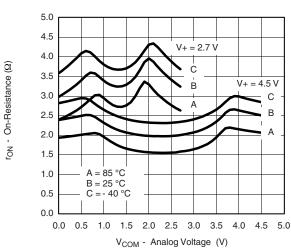
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

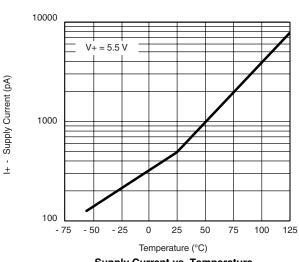




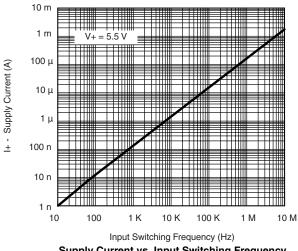




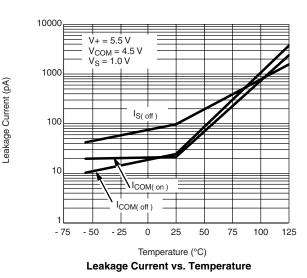
 $r_{\mbox{\scriptsize ON}}$ vs. Analog Voltage and Temperature

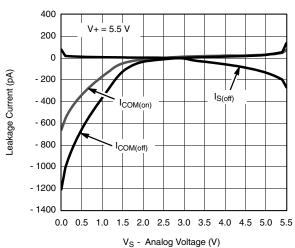


Supply Current vs. Temperature



Supply Current vs. Input Switching Frequency





Leakage vs. Analog Voltage

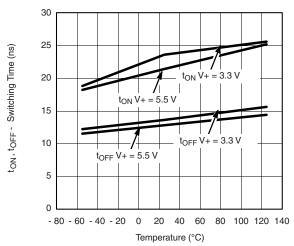




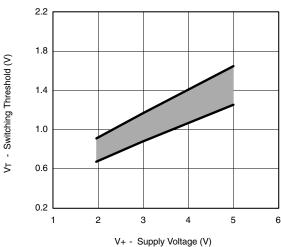
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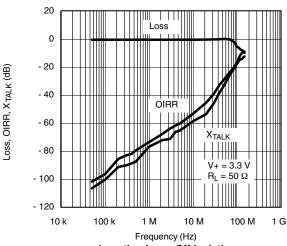
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



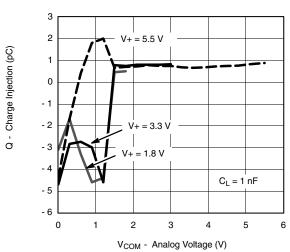
Switching Time vs. Temperature



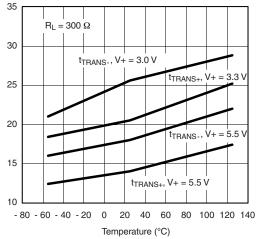
Switching Threshold vs. Supply Voltage



Insertion Loss, Off-Isolation Crosstalk vs. Frequency



Charge Injection vs. Analog Voltage



Transistion Time vs. Temperature

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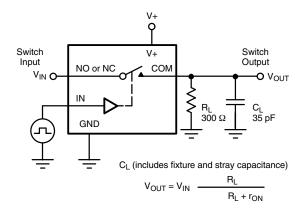
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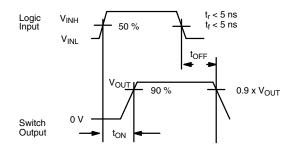
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TEST CIRCUITS







Note: Logic input waveform is inverted for switches that have the opposite logic sense control

Figure 1. Switching Time

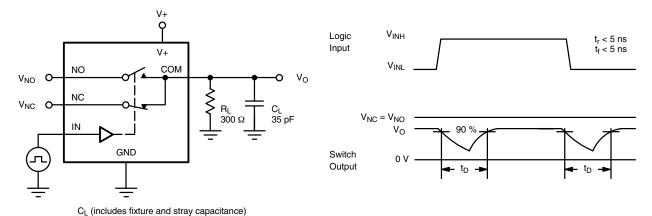
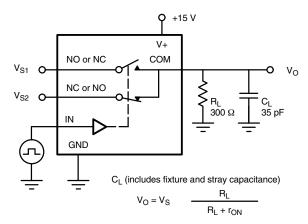


Figure 2. Break-Before-Make



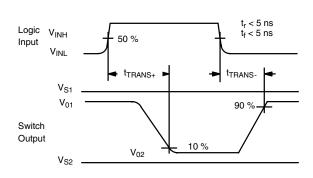


Figure 3. Transition Time

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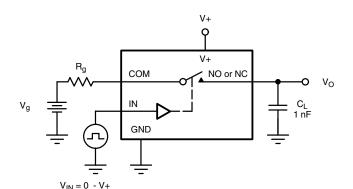


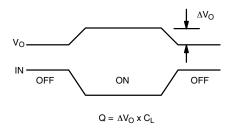


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TEST CIRCUITS





IN dependent on switch configuration Input polarity determined by sense of switch.

Figure 4. Charge Injection

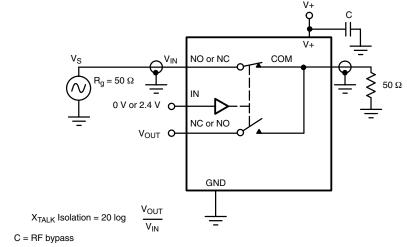
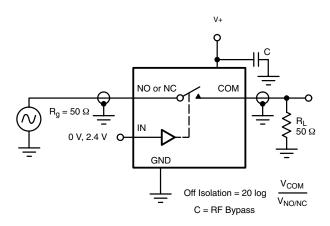
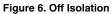


Figure 5. Crosstalk





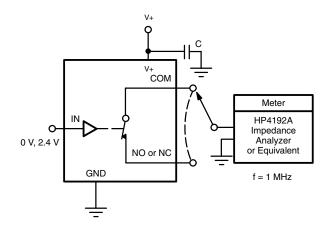


Figure 7. Source/Drain Capacitances

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?72418.

Document Number: 72418 www.vishay.com S-80164-Rev. D, 28-Jan-08

Datasheet of DG2034DN-T1-E4 - IC MULTIPLEXER 4X1 12QFN

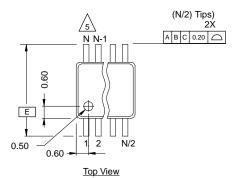
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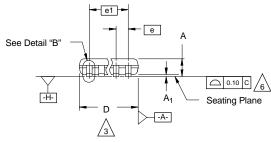


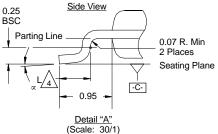
Package Information Vishay Siliconix

MSOP: 10-LEADS

JEDEC Part Number: MO-187, (Variation AA and BA)









- Die thickness allowable is 0.203 ± 0.0127 .
- Dimensioning and tolerances per ANSI.Y14.5M-1994.



Dimensions "D" and "E₁" do not include mold flash or protrusions, and are measured at Datum plane -H-, mold flash or protrusions shall not exceed



Dimension is the length of terminal for soldering to a substrate.



Terminal positions are shown for reference only.



Formed leads shall be planar with respect to one another within 0.10 mm at seating plane.



The lead width dimension does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the lead width dimension at maximum material condition. Dambar cannot be located on the lower radius or the lead foot. Minimum space between protrusions and an adjacent lead to be 0.14 mm. See detail "B" and Section "C-C".

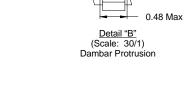


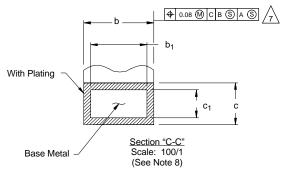
Section "C-C" to be determined at 0.10 mm to 0.25 mm from the lead tip.

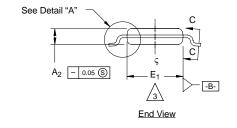
Controlling dimension: millimeters.

10. This part is compliant with JEDEC registration MO-187, variation AA and BA.

/11\ Datums -A- and -B- to be determined Datum plane -H-.







N = 10L

	MI			
Dim	Min	Nom	Max	Note
Α	-	-	1.10	
A ₁	0.05	0.10	0.15	
A ₂	0.75	0.85	0.95	
b	0.17	-	0.27	8
b ₁	0.17	0.20	0.23	8
С	0.13	-	0.23	
c ₁	0.13	0.15	0.18	
D		3.00 BSC		3
Е		4.90 BSC		
E ₁	2.90	3.00	3.10	3
е		0.50 BSC		
e ₁		2.00 BSC		
L	0.40	0.55	0.70	4
N	10			5
œ	0°	4°	6°	
ECN: T-02 DWG: 58	2080—Rev. 0 67	C, 15-Jul-02		•

Exposed pad area in bottom side is the same as teh leadframe pad size.

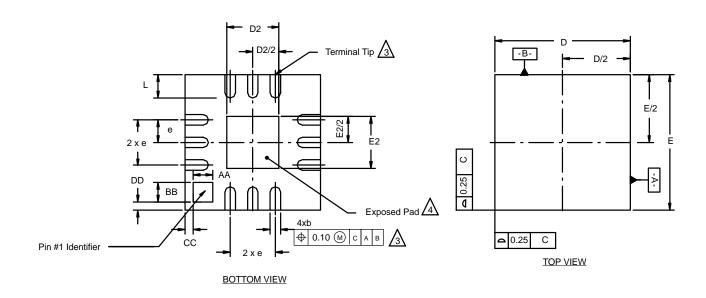
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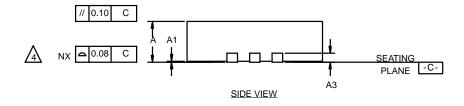
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Package Information Vishay Siliconix

QFN-12 LEAD (3 X 3)





NOTES:

- 1. All dimensions are in millimeters.
- 2. N is the total number of terminals.



Dimension b applies to metallized terminal and is measured between 0.25 and 0.30 mm from terminal tip. $\,$



Coplanarity applies to the exposed heat sink slug as well as the terminal.

The pin #1 identifier may be either a mold or marked feature, it must be located within the zone iindicated.

	МІ	MILLIMETERS			INCHES			
Dim	Min	Nom	Max	Min	Nom	Max		
Α	0.80	0.90	1.00	0.032	0.035	0.039		
b	0.18	0.23	0.30	0.007	0.012			
D		3.00 BSC			0.118 BSC			
D2	1.00	1.15	1.25	0.039	0.045	0.049		
E	3.00 BSC			0.118 BSC				
E2	1.00	1.15	1.25	0.039 0.045 0.049				
е	0.50 BSC			0.02 BSC				
L	0.45	0.55	0.65	0.018	0.022	0.026		
AA		0.435		0.017				
BB		0.435		0.017				
CC		0.18		0.007				
DD		0.18	•	0.007				
ECN: C-03092—Rev. A, 14-Apr-03 DWG: 5898								

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